

General Description

The WST2004 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent R_{DSON} and gate charge for most of the small power switching and load switch applications.

The WST2004 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low R_{DS}(on)
- Operated at Low Logic Level Gate Drive

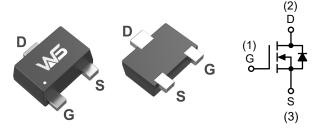
Product Summery

BV _{DSS}	R _{DSON}	I _D
20V	240mΩ	0.6A

Applications

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

SOT-723-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 8	V
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	600	mA
I _{DM}	Pulsed Drain Current ²	1.2	А
P _D @T _A =25°C	Total Power Dissipation ³	0.150	W
$R_{ heta JA}$	Thermal Resistance from Junction to Ambient (note 1)	823	°C/W
TJ	Junction Temperature	150	$^{\circ}$
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$
TL	Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	260	$^{\circ}$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	20			V	
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25℃ , I _D =1mA		0.05		V/℃	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V , I _D =0.4A		240	450		
		V_{GS} =2.5V , I_D =0.3A	280 765		765	mΩ	
1 103(ON)		V _{GS} =1.8V , I _D =0.2A		410	850		
		V _{GS} =1.5V , I _D =0.1A		450	950	mΩ	
V _{GS(th)}	Gate Threshold Voltage	\\ _\\	0.35	0.6	1.0	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=250uA$		-3.7		mV/℃	
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V , V _{GS} =0V , T _J =25℃			1	uA	
		V _{DS} =16V , V _{GS} =0V , T _J =55℃			5		
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 8V$, V_{DS} = $0V$			±10	uA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =0.1A		1.5		S	
T _{d(on)}	Turn-On Delay Time			2.9			
Tr	Rise Time	V_{DD} =15V , V_{GS} =10V ,		5.8		, no	
T _{d(off)}	Turn-Off Delay Time	$R_G=6\Omega$, $I_D=0.1A$		9		ns	
T _f	Fall Time			18			
C _{iss}	Input Capacitance			88	160		
C _{oss}	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		15	30	pF	
C _{rss}	Reverse Transfer Capacitance			10	22		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}	V =V =0V Force Current			0.1	Α
I _{SM}	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			0.5	Α
V_{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =0.2A , T _J =25℃			1.2	V

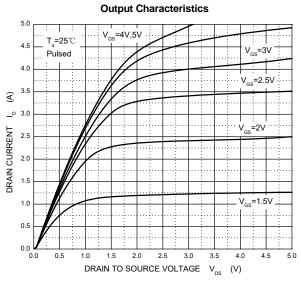
Notes:

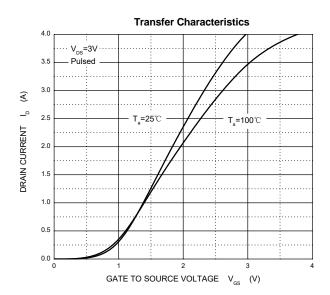
- 1. Surface mounted on FR4 board using the minimum recommended pad size.
- 2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.
- 3. Switching characteristics are independent of operating junction temperatures.
- 4. Guaranteed by design, not subject to producting.

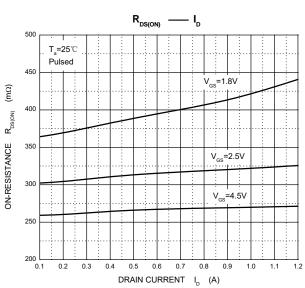


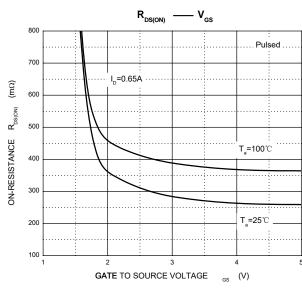
N-Ch MOSFET

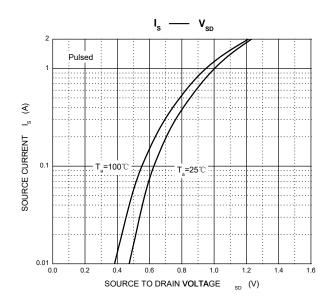
Typical Performance Characteristics

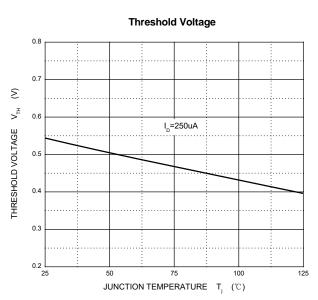






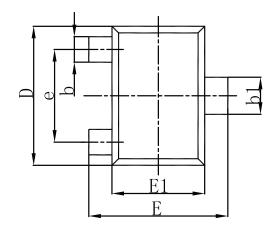


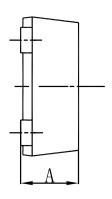


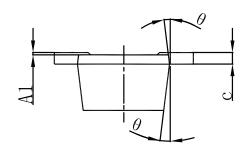




Packaging information







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	0.430	0.500	0.017	0.020	
A1	0.000	0.050	0.000	0.002	
b	0.170	0.270	0.007	0.011	
b1	0.270	0.370	0.011	0.015	
С	0.080	0.150	0.003	0.006	
D	1.150	1.250	0.045	0.049	
E	1.150	1.250	0.045	0.049	
E1	0.750	0.850	0.030	0.033	
е	0.800TYP.		0.031TYP.		
θ	7° REF.		7° REF.		



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